

MSCSM70TAM05TPAG
Datasheet
Triple Phase Leg SiC MOSFET Power Module

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a  **MICROCHIP** company

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1 Revision History

The revision history describes the changes that were implemented in the document. The changes are listed by revision, starting with the most current publication.

1.1 Revision 1.0

Revision 1.0 was published in April 2020. It is the first publication of this document.

2 Product Overview

The MSCSM70TAM05TPAG device is a triple phase leg 700 V/349 A full silicon carbide (SiC) power module.

Figure 1 • MSCSM70TAM05TPAG Electric Schematic

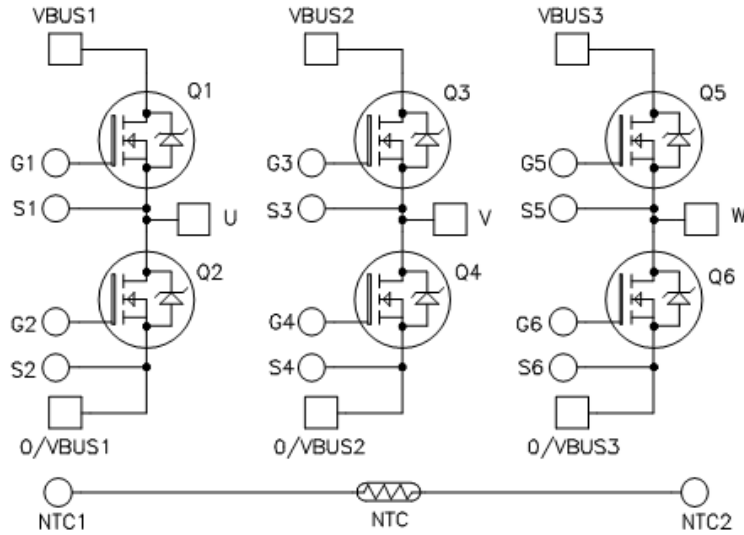
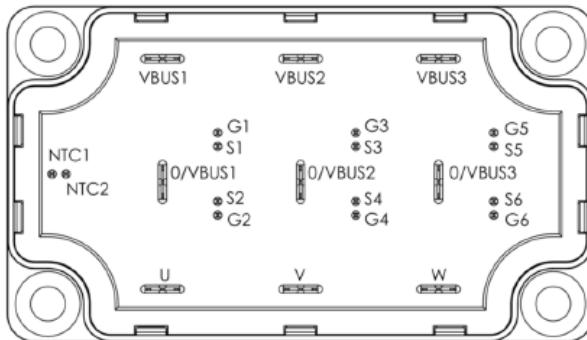


Figure 2 • MSCSM70TAM05TPAG Pinout Location



All ratings at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified.

Caution: These devices are sensitive to electrostatic discharge. Proper handling procedures should be followed.

2.1 Features

The following are key features of the MSCSM70TAM05TPAG device:

- SiC Power MOSFET
 - Low $R_{DS(on)}$
 - High-speed switching
 - Ultra low loss
- Very low stray inductance
- Kelvin source for easy drive
- Internal thermistor for temperature monitoring
- Aluminum nitride (AlN) substrate for improved thermal performance

2.2 Benefits

The following are benefits of the MSCSM70TAM05TPAG device:

- High-efficiency converter
- Outstanding performance at high-frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- Solderable terminals for power and signal, for easy PCB mounting
- Low profile
- RoHS compliant

2.3 Applications

The MSCSM70TAM05TPAG device is designed for the following applications:

- Uninterruptible power supplies
- Switched mode power supplies
- EV motor and traction drive
- Welding converters

3 Electrical Specifications

This section shows the electrical specifications of the MSCSM70TAM05TPAG device.

3.1 SiC MOSFET Characteristics (Per MOSFET)

The following table shows the absolute maximum ratings per SiC MOSFET of the MSCSM70TAM05TPAG device.

Table 1 • Absolute Maximum Ratings

Symbol	Parameter	Max Ratings	Unit
V_{DSS}	Drain-source voltage	700	V
I_D	Continuous drain current	$T_C = 25\text{ }^\circ\text{C}$	349 ¹
		$T_C = 80\text{ }^\circ\text{C}$	278 ¹
I_{DM}	Pulsed drain current	700	
V_{GS}	Gate-source voltage	-10/25	V
$R_{DS(on)}$	Drain-source ON resistance	6.4	m Ω
P_D	Power dissipation	$T_C = 25\text{ }^\circ\text{C}$	966

Note:

1. Specification of the SiC MOSFET device, but output current must be limited due to size of power connectors.

The following table shows the electrical characteristics per SiC MOSFET of the MSCSM70TAM05TPAG device.

Table 2 • Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}; V_{DS} = 700\text{ V}$			300	μA
$R_{DS(on)}$	Drain-source on resistance	$V_{GS} = 20\text{ V}$ $I_D = 120\text{ A}$	$T_J = 25\text{ }^\circ\text{C}$	5	6.4	m Ω
			$T_J = 175\text{ }^\circ\text{C}$		6.3	
$V_{GS(th)}$	Gate threshold voltage	$V_{GS} = V_{DS}, I_D = 12\text{ mA}$	1.9	2.4		V
I_{GSS}	Gate-source leakage current	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$			300	nA

The following table shows the dynamic characteristics per SiC MOSFET of the MSCSM70TAM05TPAG device.

Table 3 • Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input capacitance	$V_{GS} = 0\text{ V}$ $V_{DS} = 700\text{ V}$ $f = 1\text{ MHz}$		13.5		nF
C_{oss}	Output capacitance			1.5		
C_{rss}	Reverse transfer capacitance			0.09		
Q_g	Total gate charge	$V_{GS} = -5\text{ V}/20\text{ V}$ $V_{Bus} = 470\text{ V}$ $I_D = 120\text{ A}$		645		nC
Q_{gs}	Gate-source charge			174		
Q_{gd}	Gate-drain charge			105		
$T_{d(on)}$	Turn-on delay time	$V_{GS} = -5\text{ V}/20\text{ V}$ $V_{Bus} = 400\text{ V}$ $I_D = 240\text{ A}; T_J = 150\text{ }^\circ\text{C}$ $R_{Gon} = 9\text{ }\Omega; R_{Goff} = 1.6\text{ }\Omega$		40		ns
T_r	Rise time			35		
$T_{d(off)}$	Turn-off delay time			50		
T_f	Fall time			20		
E_{on}	Turn on energy	Inductive switching	$T_J = 150\text{ }^\circ\text{C}$	1.96		mJ
E_{off}	Turn off energy	$V_{GS} = -5\text{ V}/20\text{ V}$ $V_{Bus} = 400\text{ V}$ $I_D = 160\text{ A}$ $R_{Gon} = 9\text{ }\Omega$ $R_{Goff} = 1.6\text{ }\Omega$	$T_J = 150\text{ }^\circ\text{C}$	0.56		mJ
R_{Gint}	Internal gate resistance			1.9		Ω
R_{thJC}	Junction-to-case thermal resistance				0.155	$^\circ\text{C}/\text{W}$

The following table shows the body diode ratings and characteristics per SiC MOSFET of the MSCSM70TAM05TPAG device.

Table 4 • Body Diode Ratings and Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{SD}	Diode forward voltage	$V_{GS} = 0\text{ V}; I_{SD} = 120\text{ A}$		3.4		V
		$V_{GS} = -5\text{ V}; I_{SD} = 120\text{ A}$		3.8		
t_{rr}	Reverse recovery time	$I_{SD} = 120\text{ A}; V_{GS} = -5\text{ V}$ $V_R = 400\text{ V}; d_i/dt = 3000\text{ A}/\mu\text{s}$		38		ns
Q_{rr}	Reverse recovery charge			954		nC
I_{rr}	Reverse recovery current				44	

3.2 Thermal and Package Characteristics

The following table shows the package characteristics of the MSCSM70TAM05TPAG device.

Table 5 • Thermal and Package Characteristics

Symbol	Characteristic	Min	Max	Unit		
V _{ISOL}	RMS isolation voltage, any terminal to case t = 1 min, 50 Hz/60 Hz	4000		V		
T _J	Operating junction temperature range	-40	175	°C		
T _{JOP}	Recommended junction temperature under switching conditions	-40	T _{Jmax} -25			
T _{STG}	Storage temperature range	-40	125			
T _C	Operating case temperature	-40	125			
Torque	Mounting torque	To heatsink	M6	3	5	N.m
Wt	Package weight				250	g

The following table shows the temperature sensor NTC (see application note [APT0406](#) on www.microsemi.com) of the MSCSM70TAM05TPAG device.

Table 6 • Temperature Sensor NTC

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance at 25 °C		50		kΩ
ΔR ₂₅ /R ₂₅			5		%
B _{25/85}	T ₂₅ = 298.15 K		3952		K
ΔB/B	T _C = 100 °C		4		%

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature
R_T: Thermistor value at T

3.3 Typical SiC MOSFET Performance Curves

This sections shows the typical SiC MOSFET performance curves of the MSCSM70TAM05TPAG device.

Figure 3 • Maximum Thermal Impedance

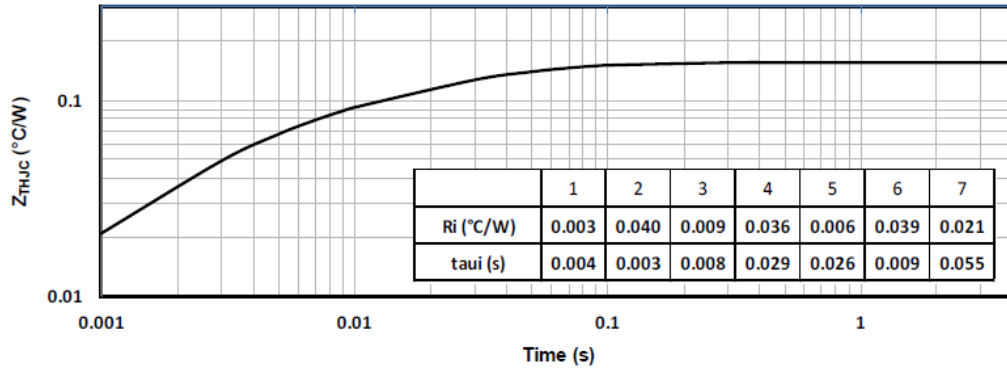


Figure 4 • Output Characteristics, $T_J = 25^\circ\text{C}$

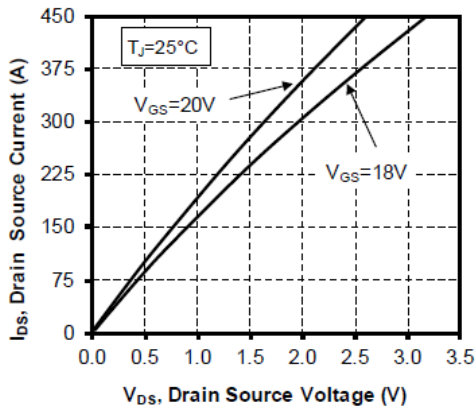


Figure 5 • Output Characteristics, $T_J = 175^\circ\text{C}$

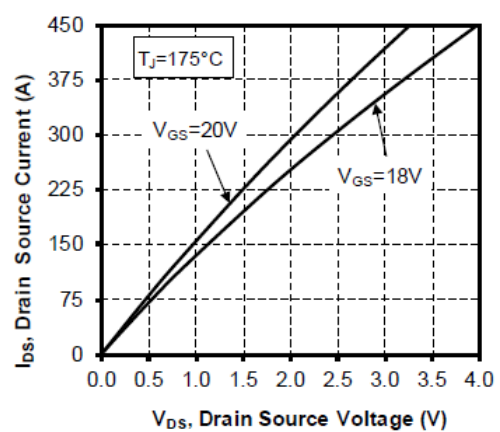


Figure 6 • Normalized $R_{DS(on)}$ vs. Temperature

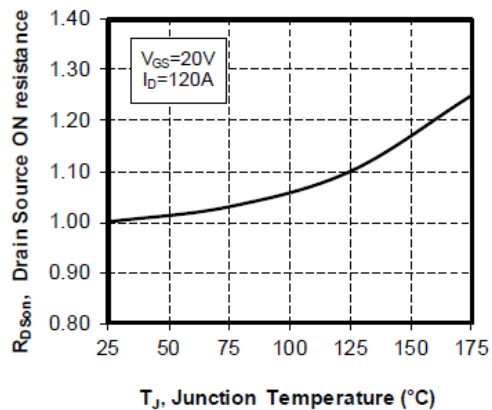


Figure 7 • Transfer Characteristics

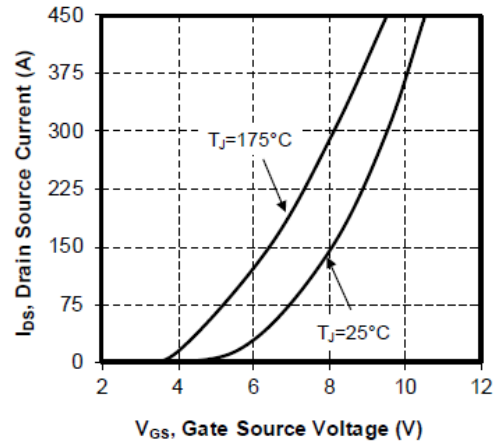


Figure 8 • Capacitance vs. Drain Source Voltage

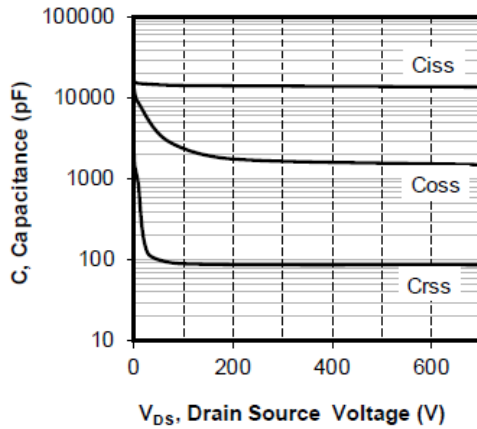


Figure 9 • Gate Charge vs. Gate Source Voltage

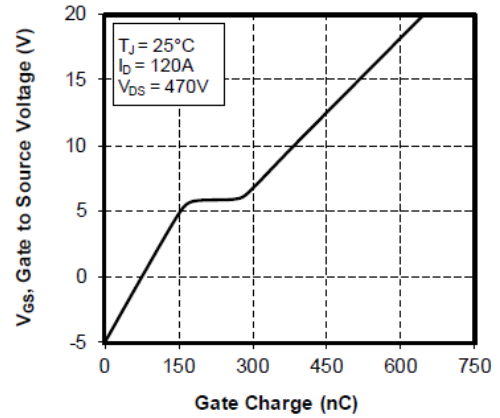


Figure 10 • Body Diode Characteristics, $T_J = 25^\circ\text{C}$

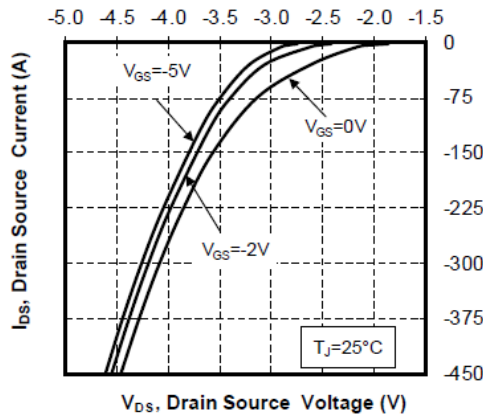


Figure 11 • 3rd Quadrant Characteristics, $T_J = 25^\circ\text{C}$

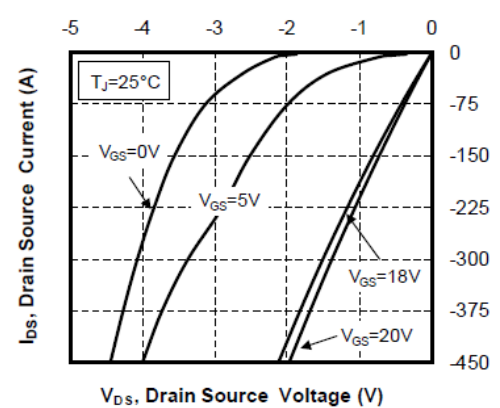


Figure 12 • Body Diode Characteristics, $T_J = 175^\circ\text{C}$

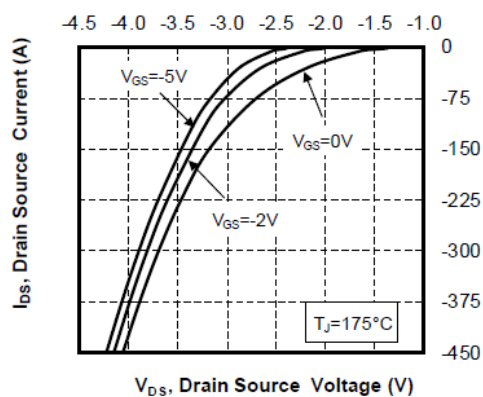


Figure 13 • 3rd Quadrant Characteristics, $T_J = 175^\circ\text{C}$

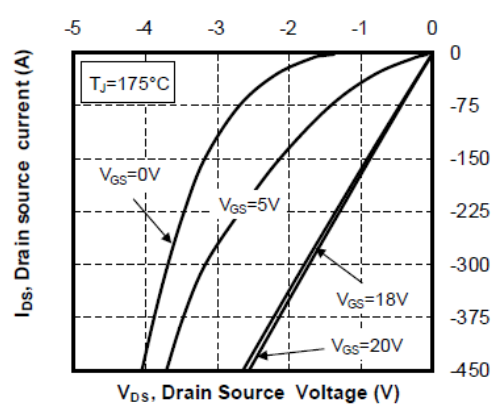


Figure 14 • Switching Energy vs. Current

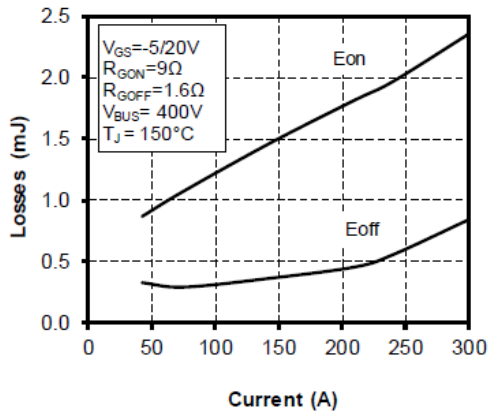


Figure 15 • Turn On Energy vs. Rg

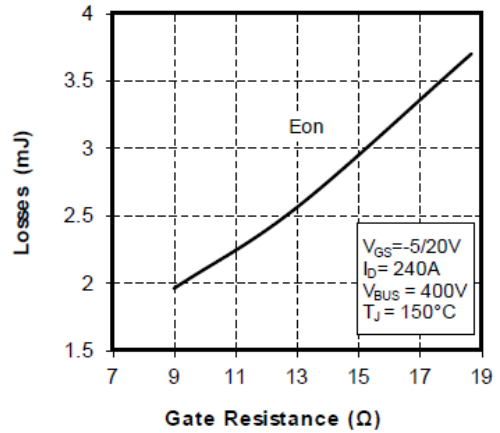


Figure 16 • Turn Off Energy vs. Rg

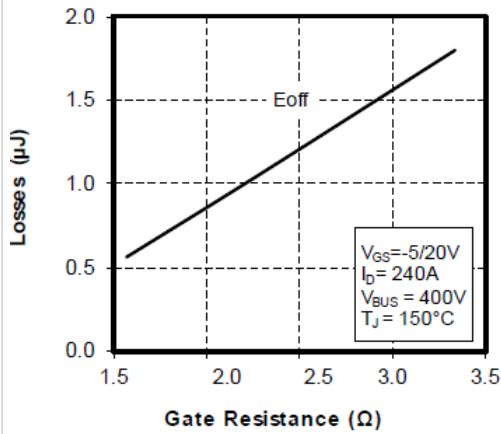
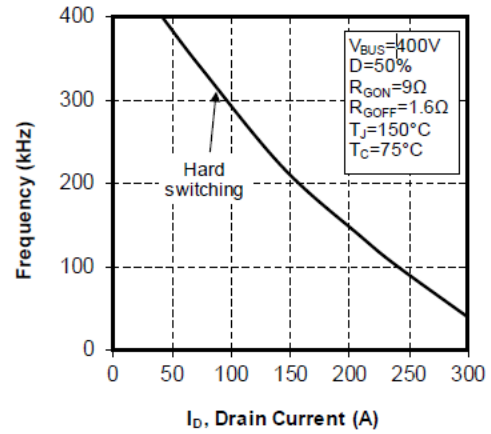


Figure 17 • Operating Frequency vs Drain Current



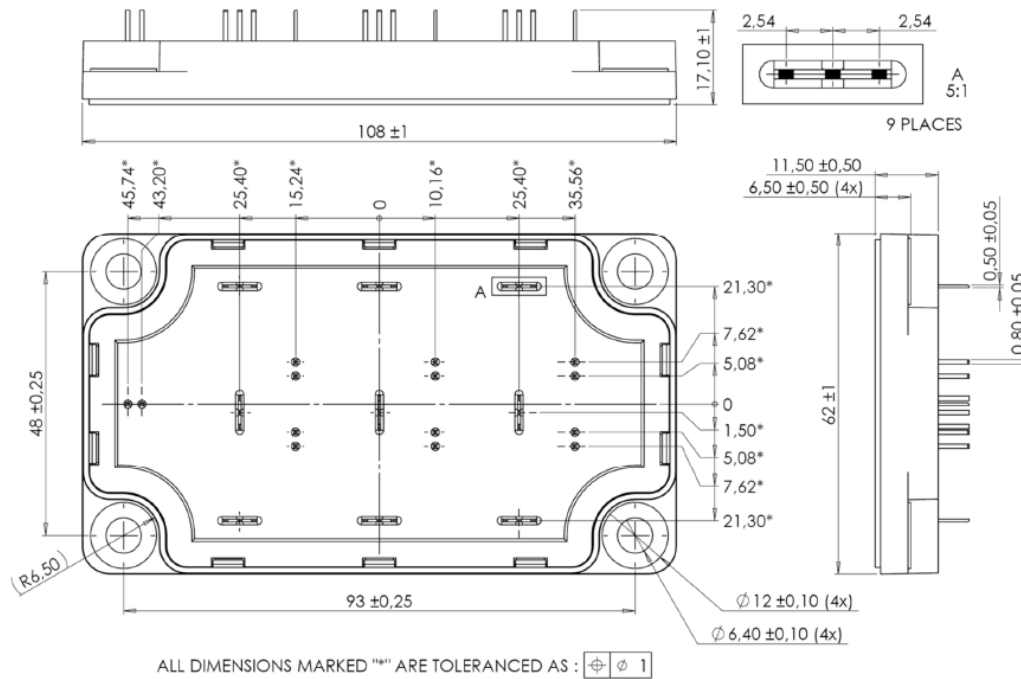
4 Package Specifications

This section shows the package specification of the MSCSM70TAM05TPAG device.

4.1 Package Outline Drawing

This section shows the package outline drawing of the MSCSM70TAM05TPAG device. The dimensions in the following figure are in millimeters.

Figure 18 • Package Outline Drawing



Note: See application note [1902 - Mounting Instructions for SP6-P \(12 mm\) Power Modules](#) on www.microsemi.com.